

Identifying the Molecular Structures of Intermediates for Optimizing the Fabrication of High-Quality Perovskite Films

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Supporting Information

ABSTRACT: During the past two years, the introduction of DMSO has revolutionized the fabrication of high-quality pervoskite MAPbI₃ (MA = CH_3NH_3) films for solar cell applications. In the developed DMSO process, the formation of $(MA)_2Pb_3I_8$ ·2DMSO (shorted as Pb_3I_8) has well recognized as a critical factor to prepare high-quality pervoskite films and thus accomplish excellent performances in perovskite solar cells. However, Pb_3I_8 is an I-deficient intermediate and must further react with methylammonium iodide (MAI) to be fully converted into MAPbI₃. By capturing and solving the molecular structures of several intermediates involved in the fabrication of perovskite films, we report in this work that the importance of DMSO is **NOT** due to the formation of Pb_3I_8 . The use of different PbI_2 ·DMSO ratios leads to two different structures of PbI_2 ·DMSO precursors (PbI_2 ·DMSO and PbI_2 ·2DMSO), thus dramatically influencing the quality of fabricated perovskite films. However, such an influence can be minimized when the PbI_2 -DMSO precursor films are thermally treated to create mesoporous



 PbI_2 films before reacting with MAI. Such a development makes the fabrication of high-quality pervoskite films highly reproducible without the need to precisely control the PbI_2 :DMSO ratio. Moreover, the formation of ionic compound $(MA)_4PbI_6$ is observed when excess MAI is used in the preparation of perovskite film. This I-rich phase heavily induces the hysteresis in PSCs, but is readily removed by isopropanol treatment. On the basis of all these findings, we develop a new effective protocol to fabricate high-performance PSCs. In the new protocol, high-quality perovskite films are prepared by simply treating the mesoporous PbI_2 films (made from PbI_2 -DMSO precursors) with an isopropanol solution of MAI, followed by isopropanol washing. The best efficiency of fabricated MAPbI_3 PSCs is up to 19.0%. As compared to the previously reported DMSO method, the devices fabricated by the method reported in this work display narrow efficiency distributions in both forward and reverse scans. And the efficiency difference between forward and reverse scans is much smaller.

INTRODUCTION

Perovskite solar cells (PSCs) have been emerging as one of the most promising candidates for next generation solar cells in view of their high efficiency, simple solution-processed technique and low cost.^{1–10} Enormous researches have been devoted to develop various approaches for continuous improvement of PSCs' performance. For example, interface engineering has been extensively attempted to optimize the contacts of perovskite layer with the electron or hole transport layers.^{11–16} Together with the composition of perovskites, ^{10,17–19} the quality control over the perovskite films has also attracted much research attention.^{10,20–27} Recently, a certified PSCs' efficiency over 20% was achieved by introducing dimethyl sulfoxide (DMSO) into perovskite precursor solution to prepare high quality perovskite films.¹⁰ Studies revealed that, as a coordinative solvent for PbI₂ and methylammonium iodide

(MAI), and thus helped to improve the quality of fabricated perovskite films.^{28–31} However, it has been noted that the amount of DMSO introduced in the system was very critical. The molar ratio of PbI₂:DMSO was found to be constrained to a quite narrow window around $1:1.^{30,31}$ It still remains unclear why the PbI₂:DMSO ratio could not be extended into a much wider region to make the fabrication of high-efficient PSCs more easily controlled and reproducible.

Moreover, with the use of DMSO, an intermediate phase $(MA)_2Pb_3I_8$; 2DMSO (denoted as Pb_3I_8) has been often identified.^{32,33} Chemically, compared to perovskite, Pb_3I_8 is an I-deficient structure and needs to further react with MAI to form perovskite. Very recently, three different transition pathways from Pb_3I_8 to perovskite under different annealing

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conditions have been investigated.³⁴ However, research effort understanding the role of Pb_3I_8 is very limited. It is still unclear whether the formation of the Pb_3I_8 intermediate is a prerequirement for the fabrication of high-quality perovskite films. The molecular understanding on how DMSO and Pb_3I_8 are involved in the formation of high-quality perovskite films is thus crucial to further improve the performance of PSCs made by the developed DMSO method.

By capturing several intermediates involved in the fabrication of perovskite films with the introduction of DMSO and resolving their molecular structures, we report in this work the molecular insight on how the amount of DMSO influences the quality of perovskite films as well as their cell performances. Systematic studies revealed that different amount of DMSO would change the form of PbI₂ and thus influence the film quality of PbI₂ precursors and their reactivity. With the PbI2:DMSO molar ratio at 1:1, a PbI2:DMSO complex was produced. The complex readily grew on substrates as a continuous high-quality film with small crystallite domains and thus good reactivity toward the formation of perovskite films. The formation of the Pb₃I₈ intermediate during the perovskite fabrication process is NOT a key factor for constructing high-efficiency PSC devices. Also, the I-rich ionic compound (MA)₄PbI₆ was found to form with the presence of excess MAI during preparation of perovskite film, which was evidently revealed to induce the hysteresis in corresponding PSCs. Based on these findings, a highly reproducible protocol using mesoporous PbI₂ films derived from PbI₂-DMSO complexes was developed for the preparation of high-quality perovskite film without the need to precisely control the PbI2:DMSO molar ratio in the fabrication. Furthermore, simply treating the mesoporous PbI₂ films with an isopropanol (IPA) solution of MAI followed by IPA washing to avoid the involvement of excess ionic compound during the fabrication of perovskite films, afforded high quality perovskite films as well reproducible PSCs devices with negligible hysteresis.

RESULTS AND DISCUSSION

Figure 1a shows the typical protocol for preparing high-quality perovskite films either by one- or two-step method that involves the use of DMSO with the PbI₂:DMSO ratio of 1:1. We employed both one- and two-step methods to fabricate PSCs devices. The fabricated PSCs had a typical p-i-n configuration of FTO/TiO₂/MAPbI₃/Spiro-OMeTAD/Au. As shown in Figure S1, S2 and Table S1, the best cell efficiencies reached to 18.4% for one-step and 18.0% for two-step methods. A small hysteresis was still observed on the fabricated devices. However, as presented in the histograms for all independently prepared 30 cells (Figure 1b,c), rather broad distributions of overall efficiencies were revealed in the reverse scan (RS: 17.2 \pm 1.2% for one-step and 16.6 \pm 1.2% for two-step) and also in the forward scan (FS: 15.6 \pm 2.3% for one-step and 15.5 \pm 2.1% for two-step). The efficiency distribution for the forward scan was broader than that for the reverse scan.

 $Pb_{3}I_{8}$ Intermediate. As shown in Figure S3, in both oneand two-step methods, the $Pb_{3}I_{8}$ phase was formed as an important intermediate before the formation of the targeted perovskite compound, consistent with previous reports.²⁸ Yellow single crystals of pure $Pb_{3}I_{8}$ phase were prepared by diffusing diethyl ether into a mixture of PbI_{2} and MAI (1:1 molar ratio) in DMSO. Structurally, $Pb_{3}I_{8}$ can be described as triple-chains of edge-sharing PbI_{6} octahedra with all unshared apexes sitting at their sides (Figure 1d). They can be considered



Figure 1. (a) Schematic illustration of cell fabrication process by oneand two-step methods. Histogram of efficiencies among 30 cells obtained by one- (b) and two-step (c) methods. (d) Crystal structure of Pb₃I₈. (e) XRD patterns of Pb₃I₈ powder before and after annealing, and heated sample (100 °C for 5 min) of Pb₃I₈ mixing with equimolar MAI (Pb₃I₈:MAI/ Δ).

as I-terminated fragments of PbI₂. These negatively charged $\{(Pb_{3}I_{8})_{n}\}^{2n-}$ chains are charge-balanced by MA cations (Figure 1d). As compared to the Pb–I molar ratio of 1:3 in perovskite, the intermediate Pb₃I₈ phase is a compositionally I-deficient phase. As expected, simple thermal annealing of pure Pb₃I₈ led to the formation of PbI₂ together with perovskite (Figure 1e). Therefore, the PSCs fabricated from pure Pb₃I₈ films exhibited poor performances (Figure S4 and Table S1). To chemically achieve the complete conversion of Pb₃I₈ into perovskite, the equimolar MAI should be introduced to react with the Pb₂I₂ phase (Figure 1e). It should be noted that in the as-prepared perovskite films made by either one- or two-step method, no PbI₂ diffraction peaks were observed after annealing (Figure S5), indicating the existence of amorphous MAI as the reactant in perovskite precursor film. The Pb₃I₈:MAI ratio is thus important to transfer Pb₃I₈ into high-quality perovskite films. However, the precise control over the local Pb₃I₈:MAI ratio is technically hard to be achieved by either one- or two-step method, which might explain why there were broad efficiency distributions in the fabricated PSCs.

Structures of PbI₂ Precursors. Considering that the secondary reaction between Pb_3I_8 and MAI is required to obtain high-quality perovskite films, we argue that the formation of Pb_3I_8 might not be necessary to reproduce high-quality perovskite films in the reported DMSO-assisted method. Improving the quality of the precursor films with the help of DMSO could be the main reason for producing high-quality perovskite films, as reflected in the perovskite films using different PbI₂:DMSO ratios by one-step method (Figure S6). Since the Pb₃I₈ phase was formed in all DMSO-precursor films before the perovskite formation in the one-step process (Figure S7), modifying the PbI₂ precursor film in two-step method may give some useful suggestions. Considering the

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PbI₂:DMSO molar ratio was critical to fabricate efficient PSCs, we investigated in this work the detailed structures of PbI₂ intermediates using DMSO in different molar ratios by adopting two-step method. When the PbI₂:DMSO molar ratio was 1:1, the casted PbI₂ precursor films made of uniform crystalline nanorods were smooth and continuous without pinholes and cracks,³¹ possessing the consistent XRD pattern with the one simulated from the crystal structure of PbI₂·DMSO (Figure 2a). Single crystals of PbI₂·DMSO were produced by



Figure 2. (a) Comparison of simulated (dot line) and experimental (solid line) XRD patterns of PbI_2 precursor films. The crystal structures of (b) PbI_2 ·DMSO, (c) PbI_2 ·DMF, and (d) PbI_2 ·2DMSO.

diffusing toluene into DMF solution of synthesized PbI₂. DMSO powder.¹⁰ As revealed by X-ray single crystal analysis, the PbI₂·DMSO precursor consists of double-chains of edgesharing PbI₅O octahedra with all unshared apexes stabilized by DMSO (Figure 2b). Such a double-chain structure can also be structurally described as DMSO-stabilized PbI₂ fragments. It should be noted that the same PbI₂ precursor structure has been previously observed by other group.³²

A similar double-chain structure was also obtained when PbI₂ was dissolved in DMF (Figure 2c).³⁵ In the preparation of single crystals of PbI₂:2DMSO precursor, when toluene was slowly diffused into DMSO solution of PbI₂, another single crystal of PbI₂ precursor (PbI₂·2DMSO) with a single-chain structure made of edge-sharing PbI₄O₂ octahedra was obtained (Figure 2d).^{31,36} In the structure of this single-chain precursor, DMSO molecules situate and stabilize the unshared axial transpositions of the octahedra. A perfect match was observed between the measured XRD pattern of precursor film prepared with PbI₂:DMSO molar ratio of 1:2 and the simulated pattern from crystal structure of PbI₂·2DMSO (Figure 2a). These results suggest that the different PbI₂:DMSO ratios used in the two-step preparation of perovskite films led to the formation of PbI₂-DMSO precursors having different structures.

Essential Role of DMSO on the Film Quality of Pbl₂ Precursors. Due to the much weaker binding of DMF on Pb than that of DMSO, the coordinative DMF is more easily removed from the double-chain precursor than DMSO from either one- or two-chain PbI₂ precursors as evidenced by the TGA analyses (Figure S8). The relatively strong binding of DMSO on Pb would alter the film quality of the PbI₂ precursors. As seen in Figure 3a-I, without introducing



Figure 3. SEM images of PbI₂ precursor films (a) and the reaction with MAI before (b) and after (c) annealing (Δ). XRD patterns of the films obtained by reactions of PbI₂ precursors with MAI before (d) and after (e) annealing.

DMSO, the PbI₂ precursor film made in the two-step method was actually composed of large PbI₂ crystallites of ~500 nm. Then the small perovskite crystalline domains were formed on the large PbI₂ crystallites due to the easy reaction between PbI₂ and MAI (Figure 3c-I). The coverage of perovskite would then retard the further reaction of PbI₂ inside the large crystallite with MAI, often leading to the presence of untreated PbI₂ in the obtained perovskite films either without or with annealing treatments (Figure 3d,e).

In contrast, although different structures of PbI₂·DMSO and PbI₂·2DMSO formed when changing the PbI₂:DMSO ratio, the casted films were both made of much smaller crystallites, making the precursor films free of pinholes as displayed in Figure 3a-II and III. Moreover, due to the relatively strong coordination of DMSO to Pb, the reaction of both PbI₂·DMSO and PbI2·2DMSO films with MAI led to the formation of regular rod-like Pb₃I₈ intermediate films (Figure 3b-II and III, and Figure 3d). Consequently, pure perovskite films with much larger crystalline domains than that prepared in the absence of DMSO (Figure 3c-II and III, and Figure 3e) were produced. Noticeably, in the case of perovskite films obtained by PbI₂. 2DMSO precursor, although the perovskite crystallites were rather large, pinholes were still observed (Figure 3c-III). The resulting large number of pinholes might be due to the presence of large content of DMSO in the precursor films. The above observations indicate that the amount of DMSO determined the quality of perovskite films in the following two aspects: (1) It altered the film quality of PbI_2 precursors. (2) It modified the reactivity of PbI₂ precursors and thus determined the crystalline domain size in the perovskite films.

High-Quality Perovskite Films from Mesoporous Pbl₂. To exclude the different reactivity of PbI₂ precursors, we therefore thermally treated the precursor films to convert them into mesoporous PbI₂ films with the hope that the mesoporous channels would facilitate the penetration of MAI to react with PbI₂ for forming high-quality perovskite films.^{37–39} The PbI₂:DMSO and PbI₂:2DMSO precursor films were transformed into the mesoporous PbI₂ films when heated at 80 °C (Figure 4a–c and S9–S11). While a relatively dense PbI₂ film



Figure 4. (a) Schematic illustration of cell fabrication process with mesoporous PbI₂ film. SEM images (b–d) and XRD patterns (e) of PbI₂·DMSO films before and after heating (Δ), and subsequently obtained perovskite film. A representative cross-sectional SEM image (f), the best J-V data (g) and histogram of cell efficiencies among 30 cells (h) produced by mesoporous PbI₂ film.

was produced by the same thermal treatment on the PbI₃:DMF precursor film due to the easy escape of coordinative DMF (Figure S9). High-quality perovskite films were readily prepared by reacting the mesoporous PbI₂ films with MAI (Figure 4d and S9). In such a protocol, the formation of Pb_3I_8 was not detected (Figure 4e and S11). As monitored by SEM (Figure S12), there was negligible change in the films' thickness when MAI was dropped onto the mesoporous PbI₂ films to allow them to be fully converted into perovskite films. In contrast, the reaction of MAI with the PbI_2 layer made in the absence of DMSO showed a double thickness expansion due to the lattice expansion from PbI₂ to perovskite. High-performance PSCs were readily fabricated from the mesoporous PbI₂ films derived from either PbI2:DMSO or PbI2:2DMSO precursors. The as-fabricated solar cells all displayed a better performance $(17.6 \pm 1.0\%)$ than that made by the reported two-step method (16.6 \pm 1.2%) in reverse scan (Figure 4f,g,

S13a and Table S2). However, it should be noted that a relatively broader distribution ($16.6 \pm 1.5\%$) in forward scan was still observed, although it is already less than that ($15.5 \pm 2.1\%$) by the reported two-step method (Figure 4h and S13b).

l-Rich lonic Compounds. The amount of MAI drop-casted in the films is also critical to the formation of high-quality pervoskite films. In this study, perovskite films prepared by the one-step method with different PbI_2 -MAI ratios were investigated. For the samples before annealing, when MAI- PbI_2 ratio was 2, the formation of pervoskite was readily observed, as evidenced by the black color of prepared films (Figure S14) and XRD patterns (Figure 5a and S15). It is



Figure 5. XRD spectra of the films with MAI-PbI₂ ratio of 1 and 2 before (a) and after (b) annealing (Δ). Crystal structures of PbI₅ (c) and PbI₆ (d). The best *J*–*V* data in forward (FS) and reverse (RS) scans (e), and the dynamic *J*_{sc} transient processes poled with –1 V switching bias voltage (f) for the devices.

particularly interesting that a new phase also formed different from the formation of intermediate Pb3I8 phase in the film prepared with MAI-PbI₂ ratio of 1. In order to identify this new phase, the single crystals suitable for X-ray diffraction were recrystallized by diffusing CH₂Cl₂ into the DMF solution of PbI₂, MAI and DMSO with the molar ratio of 1:3:1. As shown in Figure 5c, this new phase had a I-rich composition of (MA)₃PbI₅ (denoted as PbI₅).The structure of PbI₅ can be described as anionic single-chains of corner-sharing PbI₆ octahedra that are separated by MA cations. A good match between the experimental and simulated XRD patterns (Figure S15) was observed. When the MAI-PbI₂ ratio was further increased to 3 and 4, another I-rich phase started to form with the disappearance of perovskite phase, evidenced by the color change from black to yellow again and corresponding XRD patterns (Figure S14 and S15). The new phase can be designed as $(MA)_4PbI_6$ (denoted as PbI_6), demonstrated by the perfect

match of experimental XRD pattern and simulated pattern from the crystal structure of PbI₆ reported by other group (Figure S15).³⁵ PbI₆ contains individual PbI₆ octahedra with charges balanced by MA (Figure 5d). After thermal annealing, the PbI_{6} phase was clearly observed for all films prepared with excess MAI (Figure 5b and S16). As shown in SEM images (Figure S17), no obvious crystalline domains can be visualized on the surface of these films either before or after annealing compared to the films prepared using equimolar ratio of MAI and PbI₂. The performance measurements revealed a prominent hysteresis in the representative PSC device fabricated with PbI₂:2MAI (Figure 5e and Table S3). The dynamic J_{sc} transient process analyses after electric poling were carried out on this cell to understand the above phenomena.40 The device fabricated using the equal molar ratio of MAI and PbI₂ was also measured for comparison. As shown in Figure 5f and S18, J_{sc} values for poled devices in pseudosteady state gradually increased to the same values as that in the unpoled devices within 100 s. However, the device fabricated based on PbI2:2MAI exhibited remarkably slow recovery speed. It is reasonable to argue that the existence of I-rich ionic compound (PbI_6) in the perovskite film prepared by the nonstoichiometry of PbI₂ and MAI could yield accumulated ions at the interface under electric poling. Consequently, the anomalous hysteresis would be induced (Figure 5e).

Removing I-Rich Impurities to Reduce Hysteresis. Considering that the presence of I-rich ionic compound PbI_6 could be one of the reasons for the hysteresis in PSCs, the removal of this compound would help to reduce the hysteresis. Then IPA was proposed to wash the synthesized PbI_6 powder sample obtained by adding CH_2Cl_2 into the DMF solution of PbI_2 and MAI with molar ratio of 1:4. The purity of powder sample was demonstrated by the perfect match between measured XRD pattern of as-prepared powder and the simulated pattern from crystal structure of PbI_6 (Figure 6b).³⁵ It is interesting that the conversion of PbI_6 to perovskite



Figure 6. (a) The photograph of the PbI_6 powder before (Left) and after (Right) washing by IPA, and corresponding XRD spectra (b).The best J-V data in forward (FS) and reverse (RS) scans (c), and the dynamic J_{sc} transient processes poled with -1 V switching bias voltage for the devices with MAI-PbI₂ ratio of 2 before and after IPA washing (d).

can be well fulfilled, as evidenced by the obtained black color of the powder (Figure 6a) and XRD patterns (Figure 6b). During this process, PbI_{6} ((MA)₄PbI₆) was decomposed to perovskite and MAI with the help of IPA. MAI was dissolved into IPA solution and removed, thus yielding the pure perovskite. Also, the surface morphology of the IPA-treated perovskite films became much distinct with highly crystalline domains as displayed in the representative film obtained by PbI₂:2MAI (Figure S19). As expected, the decreased hysteresis was observed (Figure 6c and Table S3) in the corresponding fabricated PSCs. The largely reduced hysteresis was also demonstrated by the obviously improved recovery speed of L_c value in the *I-V* curve for poled sample in pseudosteady state (Figure 6d and Figure S20). In fact, when the MAI-PbI₂ ratio was above 1.2, I-rich ionic compounds were already detectable (Figure S21, 22). When the IPA treatment was employed to the as-obtained perovskite films by the nonstoichiometry reaction of mesoporous PbI2 scaffold with MAI in our two-step method (Figure 4), a further decreased hysteresis $(17.0 \pm 1.1\%)$ compared to $16.6 \pm 1.5\%$ before IPA washing) in the forward scan were also accomplished (Figure S23).

Optimizing Domain Size by Reaction Dynamics. To achieve sufficient conversion of mesoporous PbI2 into perovskite, a high concentration of MAI with 50 mg/mL was used (Figure S24). However, such a high concentration MAI led to a relatively rough perovskite morphology with small grain size (~700 nm, Figure 4d) due to the formation of abundant nuclei.²¹ To construct large-scale perovskite films, the manipulation of reaction dynamics between reactant molecules (PbI₂ and MAI) is important. As shown in Figure $7a-c_{2}$ immersing the as-prepared mesoporous PbI₂ film into a hot MAI solution with a lower concentration (10 mg/mL) helped to create a MAI-rich reaction environment to achieve the complete conversion of PbI₂ to perovskite. After the conversion, the film was immersed into IPA solution about 30 s to remove the excess I-rich ionic compound PbI_6 (Figure S25), generating a pure and smooth perovskite film with $\sim 1-2$ μ m large-scale grains (Figure 7d,e). The reaction of high concentration of MAI (50 mg/mL) with mesoporous PbI₂ film gave an easy formation of PbI₆ intermediate (Figure S26), and generated a relatively rough perovskite morphology with small grain sizes (Figure S27). The performance measurement revealed the best efficiency up to 19.0% on the devices fabricated from the above obtained high-quality perovskite films (Figure 7f,g, S28 and Table S4). To verify the performance of the PSC, the stabilized efficiency output of 18.5% (Figure S29) was monitored over 200 s near the maximum power point. A narrow distribution and negligible hysteresis (18.0 \pm 1.0% for reverse scan and 17.4 \pm 1.0% for forward scan) were also achieved (Figure 7h).

CONCLUSION

The molecular reaction between PbI_2 and MAI with the introduction of DMSO was investigated in details. Five different possible intermediates were captured and structurally analyzed by X-ray single-crystals analyses. The following several findings of this study help to develop high-quality perovskite films for reproducible PSCs: (1) The formation of the Pb_3I_8 intermediate was NOT the key factor for the fabrication of high-quality pervoskite films. (2) The different PbI_2 :DMSO ratio led to the formation of two PbI_2 -DMSO precursors of different structures. (3) The incorporation of DMSO into the PbI_2 precursors facilitated the fabrication of high-quality PbI₂



Figure 7. (a) Schematic illustration of cell fabrication process. SEM images (b-d) and XRD patterns (e) of the reaction process for mesoporous PbI₂ with hot MAI solution. Cross-sectional SEM image (f) and the best J-V data (g) of an optimized PSC, and the histogram of efficiencies for 30 cells in forward (FS) and reverse (RS) scans (h).

precursor films. (4) The use of excess amount of MAI easily led to the formation of I-rich phases, such as PbI₅ and PbI₆, while these compounds were transferred to PbI₆ after annealing. The presence of PbI₆ in the perovskite films aggravated the hysteresis issue in PSCs. (5) Once treated with isopropanol, PbI6 was readily converted into perovskite. On the basis of these findings, a new highly reproducible protocol to fabricate high-performance PSCs has been developed. In the new protocol, high-quality perovskite films were prepared by simply treating the mesoporous PbI₂ films (made from PbI₂-DMSO precursors) with an isopropanol solution of MAI, followed by isopropanol washing. The best efficiency of fabricated MAPbI₃ PSCs was up to 19.0%. As compared to the previously reported DMSO method, PSCs fabricated by the method developed in this work display narrow efficiency distributions. And the efficiency difference between forward and reverse scans is much smaller.

EXPERIMENTAL SECTION

Materials. All chemicals and reagents were used as received from chemical companies without any further purification. The MAI was synthesized and purified according to the literature method.² To a stirred solution of methylamine in methanol (40 wt %, 24 mL) aqueous hydroiodic acid (57 wt %, 25 mL) was slowly added at 0 °C. After 2 h, the precipitate was collected by evaporation at 50 °C for 1 h. The as-obtained product was washed with diethyl ether three times and then finally dried at 60 °C in a vacuum oven for 24 h to afford the desired pure MAI as white crystals.

Solar Cell Fabrications. Fluorine-doped Tin Oxide (FTO) glass substrates in the dimension of 2.0 cm \times 2.0 cm were patterned by etching with zinc powder and 2 M hydrochloric acid. The substrates were then sequentially washed in ultrasonic baths of acetone, distilled water and ethanol. A compact TiO₂ blocking layer was spin-coated onto the cleaned FTO glass using 0.15 M titanium tetraisopropanolate in ethanol solution at 2000 rpm for 30 s. The substrate was then annealed at 550 °C for 30 min. After cooling to room temperature, the film was immersed into the 20 mM TiCl₄ solution at 70 °C for 30 min. After dried, a ~150 nm thick mesoporous TiO₂ film was deposited on the pretreated FTO substrate by spin-coating of the TiO₂ paste (Dyesol DSL 18NR-T) with ethanol (1:5, mass ratio), which was followed by the heating at 550 °C for 30 min.

The perovskite layers were first fabricated on TiO_2 by reported oneand two-step methods. In a typical one-step protocol, a mixture of 461 mg of PbI₂, 159 mg of MAI, 78 mg of DMSO (molar ratio 1:1:1) and 600 mg of DMF was prepared at room temperature and stirred for 1 h. The completely dissolved precursor solution was spin-coated on the prepared FTO substrate at 4000 rpm for 25 s, when 0.5 mL of diethyl ether was slowly dripped on the rotating substrate in 8 s. The obtained transparent film was then heated at 70 °C for 1 min and 100 °C for 2 min to form a dense MAPbI₃ film. In the two-step method, a mixture of 461 mg of PbI₂ and 78 mg of DMSO (molar ratio 1:1) dissolved in 600 mg of DMF was spin-coated on the prepared FTO substrate at 3000 rpm for 25 s. Subsequently, the solution of MAI in isopropanol (50 mg/mL) was directly dropped on the substrate for 15 s loading time to achieve the complete conversation of PbI₂, which was spun at 3000 rpm for 10 s and then heated at 120 °C for 20 min.

In this study, two different methods based on mesoporous PbI₂ were also developed for the fabrication of perovskite layers. Perovskite was formed by reacting mesoporous PbI₂ with MAI in the solid form or solution. In the method based on solid-solid reaction, a mixture of 461 mg of PbI₂ and 78 mg of DMSO (molar ratio 1:1) dissolved in 600 mg of DMF was spin-coated on the prepared FTO substrate at 3000 rpm for 25 s. The films were annealed at 80 °C for 5 min to prepare the mesoporous PbI₂ film. After cooling to room temperature, the solution of MAI in isopropanol (50 mg/mL) was directly dropped on the substrate for 7 s loading time, and then spun at 3000 rpm for 10 s. Finally, the substrate was heated at 120 °C for 5 min. In the method based on solid-solution reaction, the prepared mesoporous PbI₂ film was dipped into the hot solution (70 °C) of MAI in isopropanol (10 mg/mL) for 2 min. After that, the film was immersed into IPA solution about 30 s to remove the I-rich ionic compounds and then heated at 100 °C for 5 min.

After the preparation of perovskite layer, the hole transport layer solution was coated by solution process at 4000 rpm for 30 s, where Spiro-OMeTAD/chlorobenzene (72 mg/1 mL) solution was employed with the additives containing 17.5 μ L Li-TFSI/acetonitrile (520 mg/1 mL) and 28.8 μ L TBP. Finally, a 80 nm thick Au counter electrode was deposited by thermal evaporation under reduced pressure of 2 × 10⁻⁷ Torr. The active area was 0.11 cm².

Preparation of Intermediate Samples. Preparation of PbI_2 . 2DMSO crystals: PbI_2 was dissolved in DMSO and then toluene was slowly diffused into above solution to generate colorless crystals.

Preparation of PbI₂·DMSO crystals: PbI₂ was dissolved in DMSO and then toluene was slowly added. The obtained white precipitation was filtered and annealed in vacuum oven at 60 °C for 24 h. The obtained powder was redissolved into DMF and then ethanol was slowly diffused into above solution to get colorless crystals.

Preparation of PbI_2 ·DMF crystals: PbI_2 was dissolved in DMF and then acetone was slowly diffused into above solution to generate colorless crystals.

Preparation of Pb_3I_8 crystals: PbI_2 and MAI with molar ratio of 1:1 were dissolved in DMSO and then diethyl ether was slowly diffused into above solution to obtain yellow crystals.

Preparation of PbI_5 crystals: $PbI_{2^{\prime}}$ MAI and DMSO with the molar ratio of 1:3:1 were dissolved in DMF and then CH_2Cl_2 was slowly diffused into above solution to yield yellow crystals.

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Preparation of PbI_6 powder: PbI_2 and MAI with molar ratio of 1:4 were dissolved in DMF and then CH_2Cl_2 was slowly added into above solution to give yellow powder samples.

Device Characterizations. The current–voltage characteristics were recorded from a solar simulator equipped with a Keithley 2400 source meter and 300 W collimated xenon lamp (Newport) calibrated with the light intensity to 100 mW·cm⁻² at AM 1.5 G solar light condition by the certified silicon solar cell. Incident photon-to-electron conversion efficiency (IPCE) was measured on a computer-controlled IPCE system (Newport) containing a xenon lamp, a monochromator and a Keithley multimeter. The system was calibrated with the certified silicon solar cell and the IPCE data were collected at DC mode. XRD patterns were analyzed by an X-ray diffractometer (Rigaku, RINT-2500) with a Cu Ka radiation source. The surface morphology of were recorded via a SEM-4800 field-emission scanning electron microscope (SEM).

Single-Crystal Analysis. The photos of the obtained crystals were shown in Figure S30. The diffraction data of all crystals was collected on an Agilent Technologies SuperNova system using Mo K α radiation ($\lambda = 0.71073$ Å) for PbI₂·2DMSO, PbI₂·DMSO, PbI₂·DMF and Pb₃I₈, and Cu K α radiation ($\lambda = 1.5418$ Å) for PbI₅ microfocus X-ray sources at 100 K. The data was processed using CrysAlis.⁴¹ The structure was solved and refined using Full-matrix least-squares based on F^2 with program *SHELXS-97* and *SHELXL-97* within *Olex*2.^{42,43} The detailed crystallographic data and structure refinements were given in Table S5.

ASSOCIATED CONTENT

S Supporting Information

The Supporting Information is available free of charge on the ACS Publications website at DOI: 10.1021/jacs.6b04924.

Details of the XRD, SEM images and photovoltaic performances of the devices (PDF) Crystallographic data for PbI₂·2DMSO (CIF) Crystallographic data for PbI₂·DMSO (CIF) Crystallographic data for PbI₂·DMF (CIF) Crystallographic data for PbI₃ (CIF) Crystallographic data for PbI₅ (CIF)

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Notes

The authors declare no competing financial interest.

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